

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

Sheet 1 of 4

Application Number.: Unassigned
 Filing Date: Herewith
 First Named Inventor: Toshiharu Furukawa
 Art Unit: Unassigned
 Examiner Name: Unassigned
 Attorney Docket Number.: ROC920030271US1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns or Lines Where Relevant Passages or Figs. Appear
<i>dn</i>		US - 6,423,583 B1	07-23-2002	Avouris et al.	
		US - 6,515,325 B1	02-04-2003	Farnworth et al.	
		US - 2003/0168683 A1	09-11-2003	Farnworth et al.	
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<i>dn</i>		US - 2003/0178617 A1	09-25-2003	Appenzeller et al.	
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⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language translation is attached.

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and or country where published.	T ²
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		P. COLLINS et al., "Nanotubes for Electronics," Scientific American, December 2000, pp. 62-69.	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Not for submission under 37 CFR 1.99)</i>	Application Number	10777576
	Filing Date	2004-02-12
	First Named Inventor	Toshiharu Furukawa
	Art Unit	2811
	Examiner Name	Ori Nadav
	Attorney Docket Number	ROC920030271US

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	Examiner Name	Ori Nadav
	Attorney Docket Number	ROC920030271US

ON	1	THOMAS RUECKES, ET AL., Carbon Nanotube-Based Nonvolatile Random Access Memory for Molecular Computing, Science magazine, July 7, 2000, Pages 94-97, Vol. 289.	<input type="checkbox"/>
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